

Fabrizio Tamarri

List of Publications by Year in descending order

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Version: 2024-02-01

14
papers

180
citations

1937685

4
h-index

1872680

6
g-index

15
all docs

15
docs citations

15
times ranked

129
citing authors

#	ARTICLE	IF	CITATIONS
1	Activation energy in the early stage of electromigration in Al-1% Si/TiN/Ti bamboo lines. Semiconductor Science and Technology, 1995, 10, 255-259.	2.0	122
2	Drawbacks to using NIST electromigration test-structures to test bamboo metal lines. IEEE Transactions on Electron Devices, 1994, 41, 2276-2280.	3.0	18
3	Resistance changes due to Cu transport and precipitation during electromigration in submicrometric Al-0.5% Cu lines. Microelectronics Reliability, 1996, 36, 1691-1694.	1.7	13
4	Resistance decay after electromigration as the effect of mechanical stress relaxation. Microelectronics Reliability, 1993, 33, 1841-1844.	1.7	9
5	Material Properties Measurement and Numerical Simulation for Characterization of Ultra-Low-Power Consumption Hotplates. , 2007, , .		4
6	Characterization of MOS Capacitors Fabricated on n-type 4H-SiC Implanted with Nitrogen at High Dose. Materials Science Forum, 2007, 556-557, 639-642.	0.3	4
7	The Evaluation of the True Test Temperature During Wafer-Level Electromigration Tests. Materials Research Society Symposia Proceedings, 1992, 265, 289.	0.1	2
8	Fabrication of Pt-Polysilicon Thin-Film Thermopiles: A Preliminary Study. , 0, , .		2
9	Fully Ion Implanted Vertical p-i-n Diodes on High Purity Semi-Insulating 4H-SiC Wafers. Materials Science Forum, 0, 717-720, 985-988.	0.3	2
10	Room Temperature Annealing Effects on Leakage Current of Ion Implanted p⁺+</sup>+</sup>n 4H-SiC Diodes. Materials Science Forum, 0, 600-603, 1027-1030.	0.3	1
11	A comparison among different technological processes for the fabrication of polysilicon-based thermoelectric transducers. , 2006, , .		0
12	Ion Implanted p⁺+</sup>+</sup>n Diodes: Post-Implantation Annealing in a Silane Ambient in a Cold-Wall Low-Pressure CVD Reactor. Materials Science Forum, 2006, 527-529, 819-822.	0.3	0
13	Effects of N Implantation before Gate Oxidation on the Performance of 4H-SiC MOSFET. Materials Science Forum, 0, 615-617, 761-764.	0.3	0
14	Micromachined gas calibration sources based on nanometric depth microchannels. Procedia Engineering, 2010, 5, 1344-1347.	1.2	0